Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S5	9204	gate adj (insulat$3 dielectric oxide dioxide) same (clean$3 etch$3 remov$3) with (semiconductor silicon) adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:47
S6	95	S5 and (anneal$4 heat$3 thermal$2) with (nitrous adj oxide nitrogen adj monoxide n20 n>"sub.2" adj o)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:18
S7	95	S6 and (anneal$4 heat$3 thermal$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 15:53
S8	92	S7 not (@rlad>"20040830" @ad>"20040830")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/16 16:16
S9	9204	gate adj (insulat$3 dielectric oxide dioxide) same (clean$3 etch$3 remov$3) with (semiconductor silicon) adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:17
S10	8858	S9 not (@rlad>"20040830" @ad>"20040830")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/16 16:52
S11	6561	S9 and (anneal$4 heat$3 thermal$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:16
S12	534	S11 and gate adj (insulat$3 dielectric oxide dioxide) with quality	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:17
S13	44	S12 and (anneal$4 heat$3 thermal$2) with (nitrous adj oxide nitrogen adj monoxide n20)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:52
S14	44	S13 and (nitrous adj oxide nitrogen adj monoxide n20)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:19

S15	189	S12 and temperature and pressure and flow	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:51
S16	183	S15 not (@rlad>"20040830" @ad>"20040830")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/16 16:52
S17	183	S16 and (anneal$4 heat$3 thermal$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:52